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HARACI

Application Number

07/337566

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[11] Patent Number:

5,418,752

[45] Date of Patent:

May 23, 1995

[54] FLASH EEPROM SYSTEM WITH ERASE SECTOR SELECT

United States Patent [19]

[75] Inventors: Eliyahou Harari, Los Gatos; Robert D. Norman, San Jose; Sanjay

Mehrotra, Milpitas, all of Calif.

[73] Assignee: Sundisk Corporation, Santa Clara,

[21] Appl. No.: 963,851

Harari et al.

[22] Filed: Oct. 20, 1992

system ...sign", Computer Design, Mar. 1, 1989, pp. 30 and 32.

Hsuc

[57] ABSTRACT

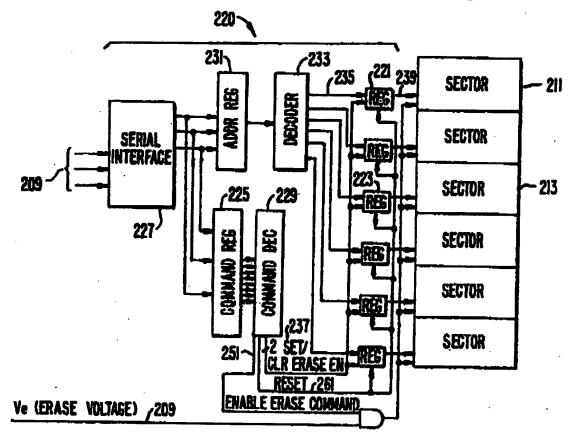
A system of F. . . . BEprom memory chips with controlling circuits ... as as non-volatile memory such as that provided by gnetic disk drives. Improvements include selective multiple sector erase, in which any combinations of Figure sectors may be erased together. Selective sectors among the selected combination may also be de-selected during the crase operation. Another improvement is the ability to remap and replace defective cells with substitute cells. The remapping is performed automatically as soon as a defective cell is detected. When the number of defects in a Plash sector becomes large, the whole sector is remapped. Yet another improvement is the use of a write cache to reduce the number of writes to the Flash EEprom memory, thereby minimizing the stress to the device from undergoing too many write/crase cycling.

Related U.S. Application Data [62] Division of Scr. No. 337,566, Apr. 13, 1989, shandoned. [51] Int. Cl. Gl1C 7/00 [52] U.S. Cl. 365/218; 365/185; 365/900 [58] Field of Search 365/185, 218, 900, 230.03 [56] References Cited U.S. PATENT DOCUMENTS [56] 4,752,871 6/1988 Sparks et al. 365/218 X [57] 4,970,692 11/1990 Ali et al. 365/218

OTHER FUBLICATIONS

R. Wilson, "1-Mbit flash memories seek their rule in

4 Claims, 5 Drawing Sheets



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